

MTD2015 SYSTEM

IGBTs and MOSFETs power modules DYNAMIC TESTER



Typical switching parameters: t_{don} , t_r , t_{on} , t_{doff} , t_f , t_{off} , E_{on} , E_{off} , I_{rr} , t_{rr} , E_{rec} , Q_{rr}

RBSOA: reverse bias safe operating area test, ILM verification (V_{clamp} 3KV)

UIS: unclamped inductive switching test, MOSFET avalanche (up to 3KV)

SCSOA: short circuit withstanding test (up to 4000A)

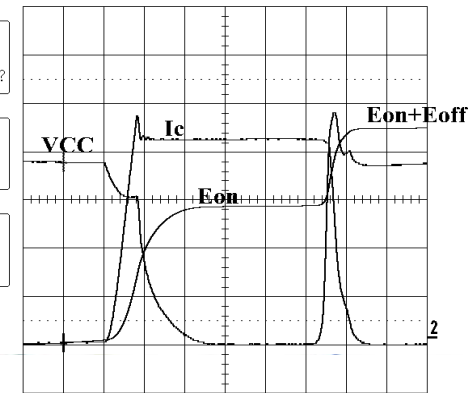
Power generation: 1.5kV-2000A

12-Nov-93
17:47:10

0: f(B+k)dt
1 μ s
3.33 mV²s
0.11 mV?

2
1 μ s
5.0 V
-0.55 V

1
1 μ s
180 V
681 V



1 μ s
1 1.00 V DC ∞

2 5 V DC ∞

Ext HFREJ 1.00 V

STOPPED